

Title (en)

IMAGE SENSOR FOR IMAGING AT A VERY LOW LEVEL OF LIGHT

Title (de)

BILDSSENSOR FÜR DIE BILDGEBUNG BEI SEHR SCHWACHER BELEUCHTUNG

Title (fr)

CAPTEUR D'IMAGE POUR IMAGERIE A TRES BAS NIVEAU DE LUMIERE

Publication

**EP 2430660 A1 20120321 (FR)**

Application

**EP 10731768 A 20100511**

Priority

- FR 2010050920 W 20100511
- FR 0953194 A 20090514

Abstract (en)

[origin: WO2010130951A1] The invention relates to a basic device for an image sensor, including a photogeneration and charge-collecting region formed at the surface of a semiconductor substrate having a first type of conductivity (30), adapted to be biased at a reference voltage, the photogeneration region being associated with a device for the transfer (36), multiplication (38, 40, 42) and insulation (44) of charges. The photogeneration region has an insulated gate (32) mounted thereon, which is adapted to be alternately biased at a first voltage and at a second voltage, the insulated gate being made of a low-absorption material.

IPC 8 full level

**H01L 27/146** (2006.01); **H01L 27/148** (2006.01)

CPC (source: EP US)

**H01L 27/14609** (2013.01 - EP US); **H01L 27/1464** (2013.01 - EP US); **H01L 27/1485** (2013.01 - EP US)

Citation (search report)

See references of WO 2010130951A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK SM TR

DOCDB simple family (publication)

**WO 2010130951 A1 20101118**; EP 2430660 A1 20120321; FR 2945668 A1 20101119; FR 2945668 B1 20111216; JP 2012527107 A 20121101; US 2012112247 A1 20120510

DOCDB simple family (application)

**FR 2010050920 W 20100511**; EP 10731768 A 20100511; FR 0953194 A 20090514; JP 2012510345 A 20100511; US 201013319895 A 20100511